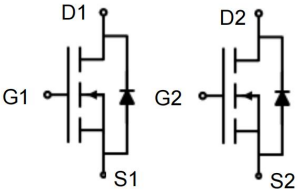
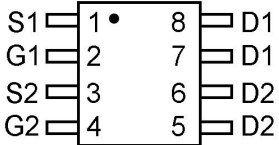



## DUAL N-Channel Enhancement Mode Power MOSFET

<p><b>Description</b></p> <p>The G800N06S2 uses advanced trench technology to provide excellent <math>R_{DS(ON)}</math>, low gate charge. It can be used in a wide variety of applications.</p> <p><b>General Features</b></p> <ul style="list-style-type: none"> <li>● <math>V_{DS}</math> 60V</li> <li>● <math>I_D</math> (at <math>V_{GS} = 10V</math>) 3A</li> <li>● <math>R_{DS(ON)}</math> (at <math>V_{GS} = 10V</math>) &lt; 80m<math>\Omega</math></li> <li>● <math>R_{DS(ON)}</math> (at <math>V_{GS} = 4.5V</math>) &lt; 85m<math>\Omega</math></li> <li>● 100% Avalanche Tested</li> <li>● RoHS Compliant</li> </ul> <p><b>Application</b></p> <ul style="list-style-type: none"> <li>● Power switch</li> <li>● DC/DC converters</li> </ul>	 <p>Schematic diagram</p>  <p>pin assignment</p>  <p>SOP-8 Dual</p>
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### Ordering Information

Device	Package	Marking	Packaging
G800N06S2	SOP-8 Dual	G800N06D	4000pcs/Reel

### Absolute Maximum Ratings $T_C = 25^\circ C$ , unless otherwise noted

Parameter	Symbol	Value	Unit
Drain-Source Voltage	$V_{DS}$	60	V
Continuous Drain Current	$I_D$	3	A
Pulsed Drain Current (note1)	$I_{DM}$	12	A
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Power Dissipation	$P_D$	1.7	W
Operating Junction and Storage Temperature Range	$T_J, T_{stg}$	-55 To 150	$^\circ C$

### Thermal Resistance

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-Ambient	$R_{thJA}$	73.5	$^\circ C/W$

Specifications $T_J = 25^\circ\text{C}$ , unless otherwise noted						
Parameter	Symbol	Test Conditions	Value			Unit
			Min.	Typ.	Max.	
<b>Static Parameters</b>						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu\text{A}$	60	--	--	V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 60V, V_{GS} = 0V$	--	--	1	$\mu\text{A}$
Gate-Source Leakage	$I_{GSS}$	$V_{GS} = \pm 20V$	--	--	$\pm 100$	nA
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu\text{A}$	0.7	0.9	1.2	V
Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS} = 10V, I_D = 3A$	--	60	80	m $\Omega$
		$V_{GS} = 4.5V, I_D = 3A$	--	65	85	
Forward Transconductance	$g_{FS}$	$V_{GS} = 5V, I_D = 3A$	--	5	--	S
<b>Dynamic Parameters</b>						
Input Capacitance	$C_{iss}$	$V_{GS} = 0V,$ $V_{DS} = 30V,$ $f = 1.0\text{MHz}$	--	458	--	pF
Output Capacitance	$C_{oss}$		--	26	--	
Reverse Transfer Capacitance	$C_{rss}$		--	23	--	
Total Gate Charge	$Q_g$	$V_{DD} = 30V,$ $I_D = 3A,$ $V_{GS} = 10V$	--	6	--	nC
Gate-Source Charge	$Q_{gs}$		--	1	--	
Gate-Drain Charge	$Q_{gd}$		--	1.3	--	
Turn-on Delay Time	$t_{d(on)}$	$V_{DD} = 30V,$ $I_D = 3A,$ $R_G = 1\Omega$	--	15	--	ns
Turn-on Rise Time	$t_r$		--	6	--	
Turn-off Delay Time	$t_{d(off)}$		--	15	--	
Turn-off Fall Time	$t_f$		--	10	--	
<b>Drain-Source Body Diode Characteristics</b>						
Continuous Body Diode Current	$I_S$	$T_C = 25^\circ\text{C}$	--	--	3	A
Body Diode Voltage	$V_{SD}$	$T_J = 25^\circ\text{C}, I_{SD} = 3A, V_{GS} = 0V$	--	--	1.2	V
Reverse Recovery Charge	$Q_{rr}$	$I_F = 3A, V_{GS} = 0V$ $di/dt=500\text{A/us}$	--	24	--	nC
Reverse Recovery Time	$T_{rr}$		--	12	--	ns

### Notes

1. Repetitive Rating: Pulse width limited by maximum junction temperature
2. Identical low side and high side switch with identical  $R_G$

### Gate Charge Test Circuit



### Switch Time Test Circuit

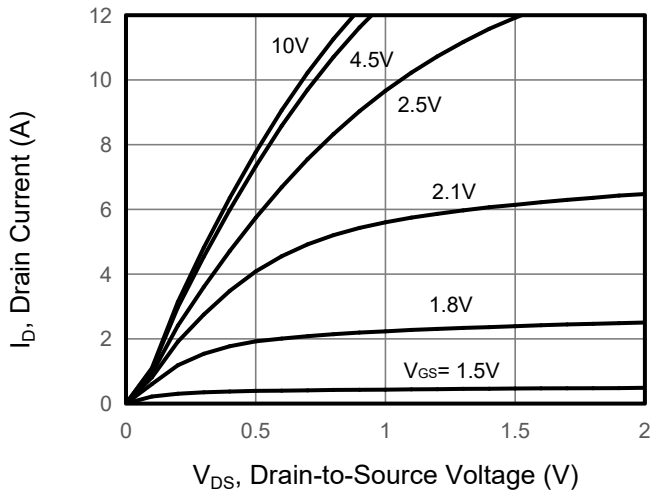


### EAS Test Circuit

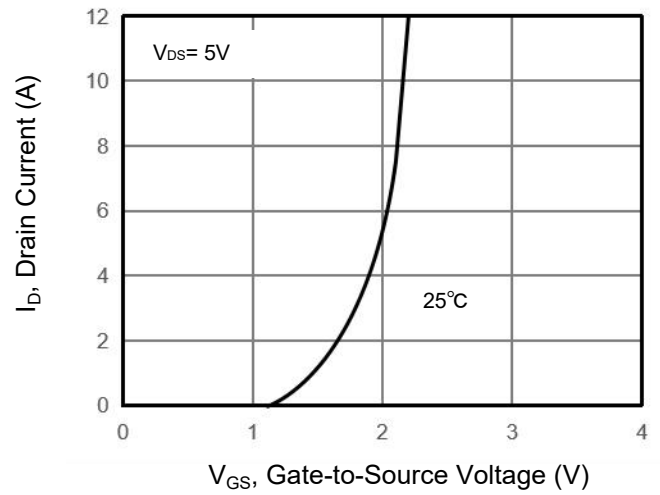


Typical Characteristics  $T_J = 25^\circ\text{C}$ , unless otherwise noted

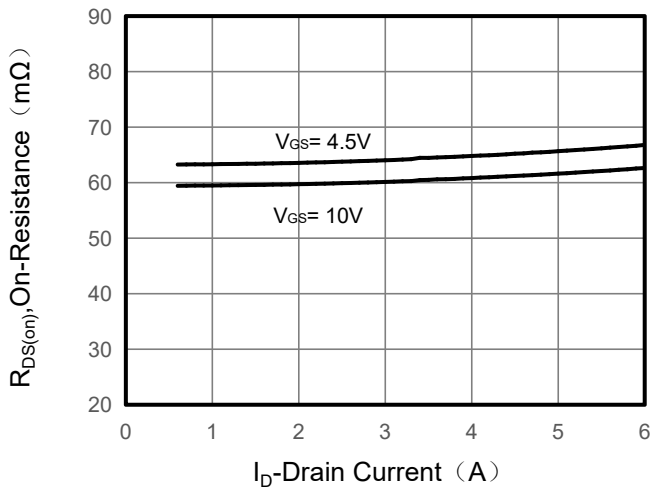
**Figure 1. Output Characteristics**



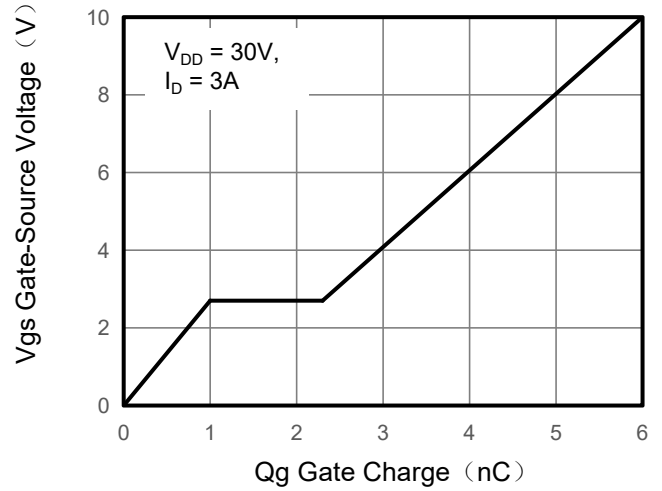
**Figure 2. Transfer Characteristics**



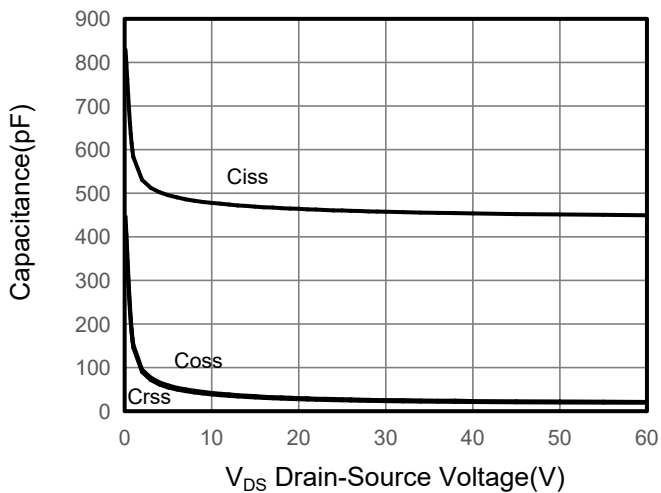
**Figure 3. Drain Source On Resistance**



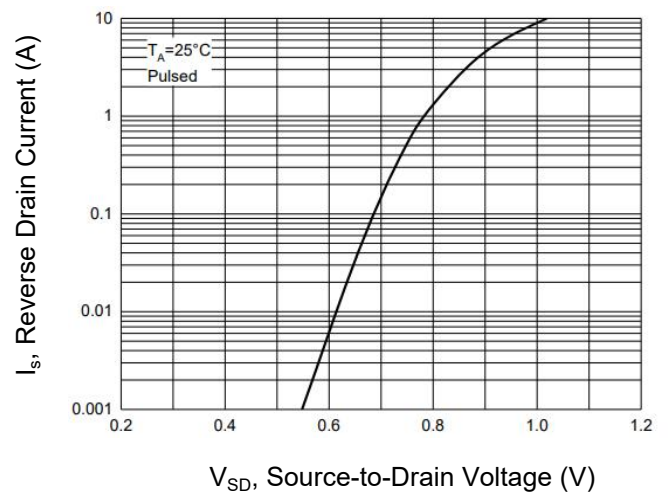
**Figure 4. Gate Charge**



**Figure 5. Capacitance**



**Figure 6. Source-Drain Diode Forward**



## Typical Characteristics $T_J = 25^\circ\text{C}$ , unless otherwise noted

Figure 7. Drain-Source On-Resistance

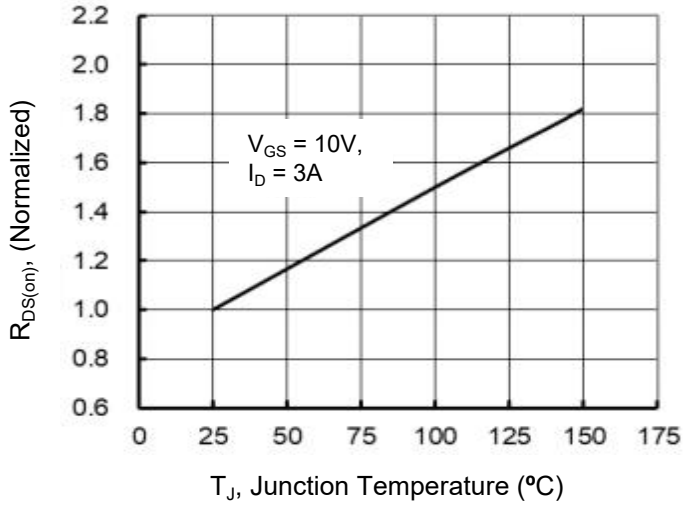


Figure 8. Safe Operation Area

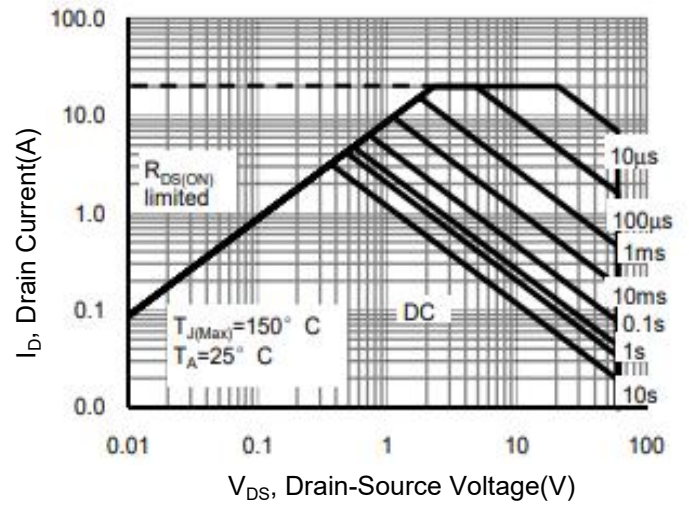
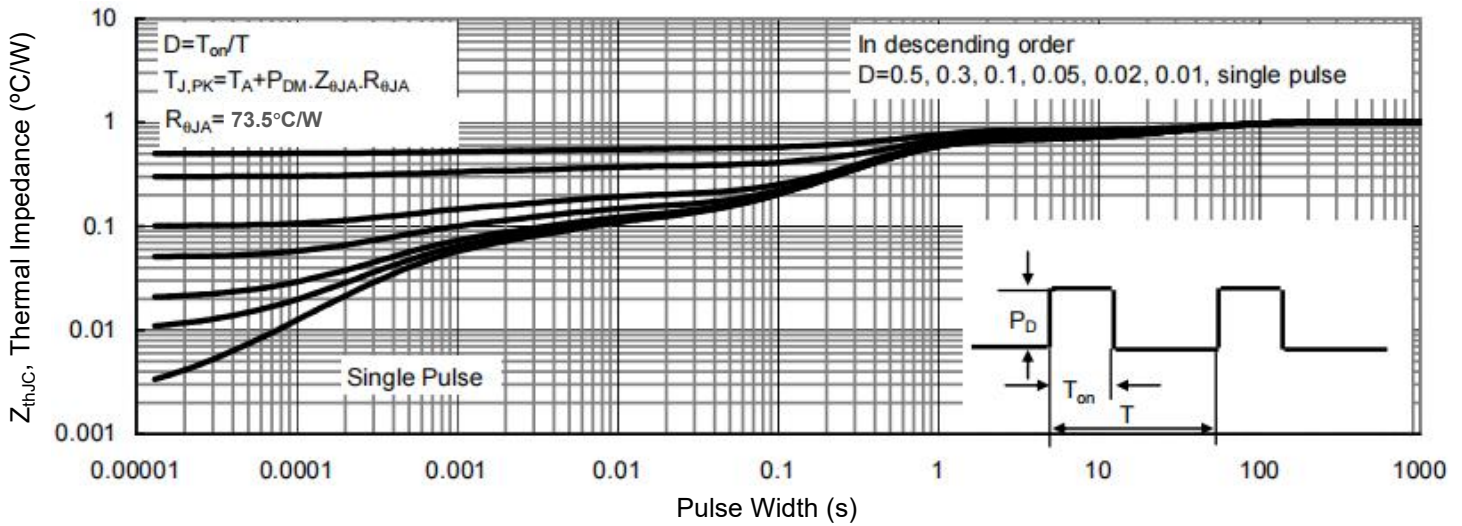
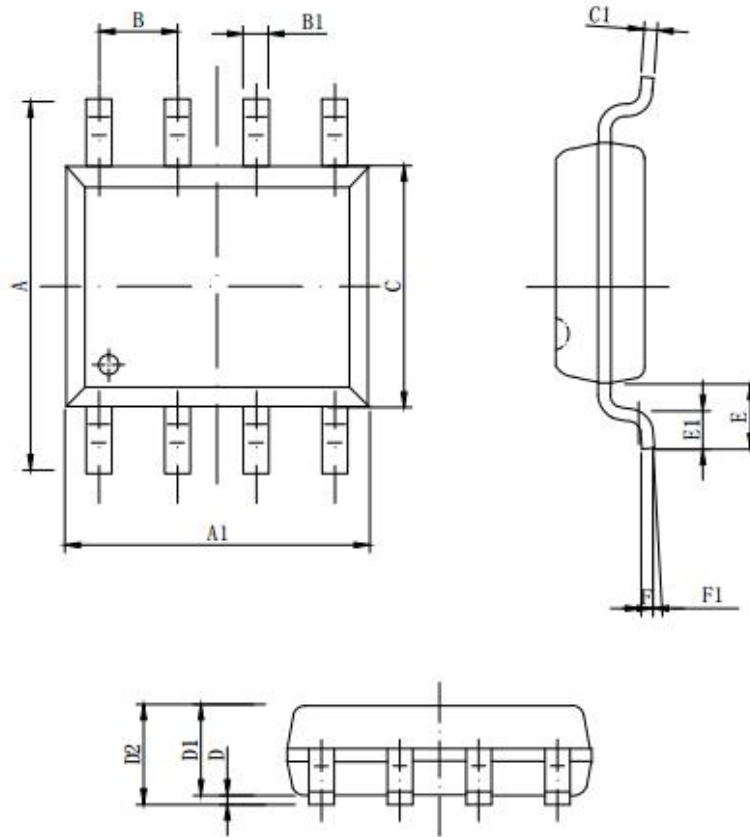


Figure 9. Normalized Maximum Transient Thermal Impedance



## SOP-8 Dual Package Information



Symbol	Dimensions in Millimeters		
	MIN.	NOM.	MAX.
A	5.800	6.000	6.200
A1	4.800	4.900	5.000
B	1.270BSC		
B1	0.35 <sup>8x</sup>	0.40 <sup>8x</sup>	0.45 <sup>8x</sup>
C	3.780	3.880	3.980
C1	--	0.203	0.253
D	0.050	0.150	0.250
D1	1.350	1.450	1.550
D2	1.500	1.600	1.700
D2	1.500	1.600	1.700
E	1.060REF		
E1	0.400	0.700	0.100
F	0.250BSC		
F1	2°	4°	6°